

# Structural phase transition induced microstructure changes in V<sub>2</sub>O<sub>3</sub> based hybrid magnetic heterostructures

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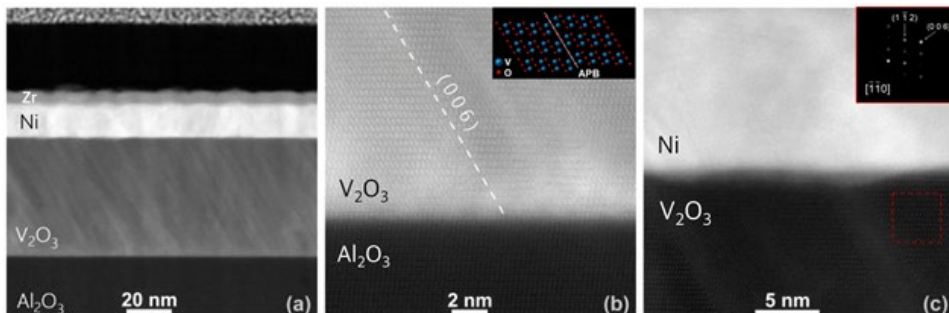
Vanadiumsesquioxide (V<sub>2</sub>O<sub>3</sub>) stands out in the realm of transition metal oxides for its distinctive and multifaceted phase transitions, offering a rich ground for exploration in the context of structural, electrical and magnetic properties [1, 2]. At room temperature, V<sub>2</sub>O<sub>3</sub> is in a rhombohedral phase, exhibiting metallic properties and upon cooling to below ~150 K it undergoes a structural phase transition to an insulating monoclinic phase. Through the transition the material also changes from a paramagnetic state to a low temperature antiferromagnetic state and has been observed to induce an exchange bias into overlying magnetic layers [3].

In this work we present an investigation on the interplay between the microstructure of V<sub>2</sub>O<sub>3</sub> thin films, deposited using reactive dc magnetron sputtering, and their structural properties during the phase transition. Specifically, we examine the changes in the microstructure during the phase coexistence region of the V<sub>2</sub>O<sub>3</sub> layer and how these changes correlate with alterations in the magnetic properties of overlying magnetic layers in V<sub>2</sub>O<sub>3</sub>/Ni heterostructures [4].

Using scanning transmission electron microscopy (STEM) using high-angle annular dark-field (HAADF-STEM) imaging, energy dispersive x-ray analysis (STEM-EDX) and electron energy loss spectroscopy (EELS) we investigate the stoichiometric composition of the films and confirm their crystalline quality at the sub-nm lateral scale and observe an atomically flat interface between the Al<sub>2</sub>O<sub>3</sub> substrate and the V<sub>2</sub>O<sub>3</sub> layer, as well as a sharp interface between V<sub>2</sub>O<sub>3</sub> and the overlying magnetic Ni layer.

The simultaneous presence of two phases in V<sub>2</sub>O<sub>3</sub> during its structural phase transition was identified with temperature dependent high resolution x-ray diffraction measurements performed at the BM28 (XMaS) beamline at the European Synchrotron Radiation Facility (ESRF) in Grenoble, France. The measurements reveal an increase in surface roughness during the transition which is attributed to the coexistence of the two phases in different regions of the film. During the phase coexistence region we observe a concomitant increase in the coercivity of the magnetic layer correlated with the increased roughness of the V<sub>2</sub>O<sub>3</sub> surface.

## Graphic:



**Keywords:**

Phase transitions, STEM, Magnetism, Heterostructures

**Reference:**

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